



NOT  
RECOMMENDED FOR  
NEW DESIGNS

T-43-21

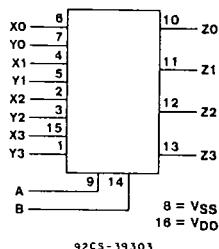
## CD4519B Types

### CMOS 4-Bit AND/OR Selector, Quad 2-Channel Data Selector, or Quad Exclusive NOR Gate

High-Voltage Types (20-Volt Rating)

#### Features:

- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20V
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1  $\mu$ A at 18 V over full package-temperature range: 100 nA at 18 V and 25° C
- Noise margin (over full package-temperature range) = 1V at  $V_{DD} = 5V$   
2V at  $V_{DD} = 10V$   
2.5V at  $V_{DD} = 15V$
- Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



FUNCTIONAL DIAGRAM

■ CD4519B CMOS types can be configured as 4-bit AND/OR selectors, as quad 2-channel data selectors, or as quad exclusive-NOR gates. This is achieved by setting the control inputs (A and B) to produce the particular function desired.

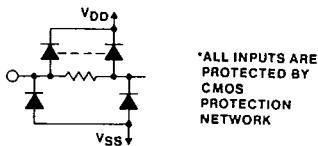
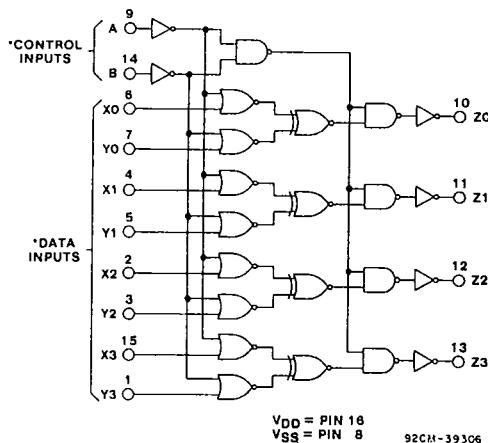


Fig. 1 - Logic diagram.

The CD4519B types are supplied in 16-lead ceramic dual-in-line packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

TRUTH TABLE

CONTROL INPUTS		OUTPUT
A	B	$Z_n$
0	0	0
0	1	$Y_n$
1	0	$X_n$
1	1	$X_n \oplus Y_n$

Note:  
 $X_n \oplus Y_n$  means  $X_n$  (Exclusive-NOR)  $Y_n$

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COMMERCIAL CMOS  
HIGH VOLTAGE ICs

*CD4519B Types**T-43-21*

## MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ )Voltages referenced to  $V_{SS}$  Terminal) ..... -0.5V to +20V

## INPUT VOLTAGE RANGE, ALL INPUTS

-0.5V to  $V_{DD}$  +0.5V

## DC INPUT CURRENT, ANY ONE INPUT

±10mA

POWER DISSIPATION PER PACKAGE ( $P_D$ ):For  $T_A = -55^\circ\text{C}$  to  $+100^\circ\text{C}$  ..... 500mWFor  $T_A = +100^\circ\text{C}$  to  $+125^\circ\text{C}$  ..... Derate Linearity at 12mW/ $^\circ\text{C}$  to 200mW

## DEVICE DISSIPATION PER OUTPUT TRANSISTOR

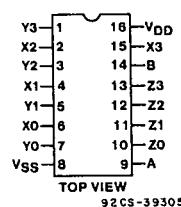
FOR  $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$  ..... 100mWOPERATING-TEMPERATURE RANGE ( $T_A$ ) ..... -55 $^\circ\text{C}$  to  $+125^\circ\text{C}$ STORAGE TEMPERATURE RANGE ( $T_{S(\text{Q})}$ ) ..... -65 $^\circ\text{C}$  to  $+150^\circ\text{C}$ 

## LEAD TEMPERATURE (DURING SOLDERING):

At distance  $1/16 \pm 1/32$  inch (1.59 ± 0.79mm) from case for 10s max .....  $+265^\circ\text{C}$ RECOMMENDED OPERATING CONDITIONS at  $25^\circ\text{C}$ 

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For $T_A = \text{Full Package Temperature Range}$ )	3	18	V



**CD4519B**  
TERMINAL ASSIGNMENT

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## STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
				+25				Min.	Typ.	Max.	
	V <sub>O</sub> (V)	V <sub>IN</sub> (V)	V <sub>DD</sub> (V)	-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I <sub>CC</sub> Max.	—	0.5	5	1	1	30	30	—	0.02	1	μA
	—	0.10	10	2	2	60	60	—	0.02	2	
	—	0.15	15	4	4	120	120	—	0.02	4	
	—	0.20	20	20	20	600	600	—	0.04	20	
Output Low (Sink) Current, I <sub>OL</sub> Min.	0.4	0.5	5	3.84	3.66	2.52	2.16	3.06	6	—	mA
	0.5	0.10	10	9.6	9	6.6	5.4	7.8	15.6	—	
	1.5	0.15	15	25.2	24	16.8	14.4	20.4	40.8	—	
	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	
Output High (Source) Current, I <sub>OH</sub> Min.	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	mA
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0.15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
	—	0.5	5	0.05				—	0	0.05	
Output Voltage: Low-Level, V <sub>L</sub> Max.	—	0.10	10	0.05				—	0	0.05	V
	—	0.15	15	0.05				—	0	0.05	
	—	0.5	5	4.95				4.95	5	—	
Output Voltage: High-Level, V <sub>H</sub> Min.	—	0.10	10	9.95				9.95	10	—	V
	—	0.15	15	14.95				14.95	15	—	
	0.5, 4.5	—	5	1.5				—	—	1.5	
Input Low Voltage, V <sub>L</sub> Max.	1.9	—	10	3				—	—	3	V
	1.5, 13.5	—	15	4				—	—	4	
	4.5	—	5	3.5				3.5	—	—	
Input High Voltage, V <sub>H</sub> Min.	9	—	10	7				7	—	—	V
	13.5	—	15	11				11	—	—	
Input Current I <sub>IN</sub> Max	—	0.18	18	±0.1	±0.1	±1	±1	—	±10 <sup>-5</sup>	±0.1	μA

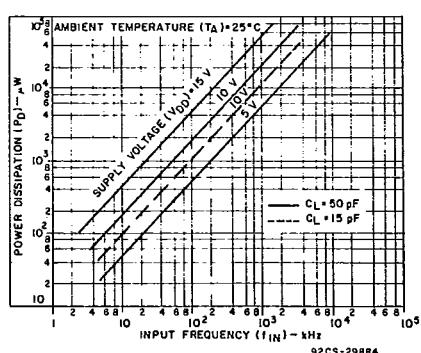
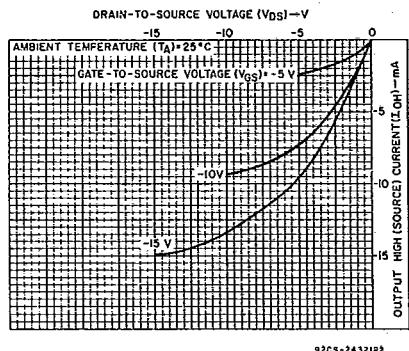
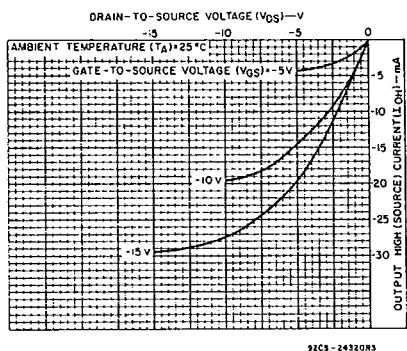
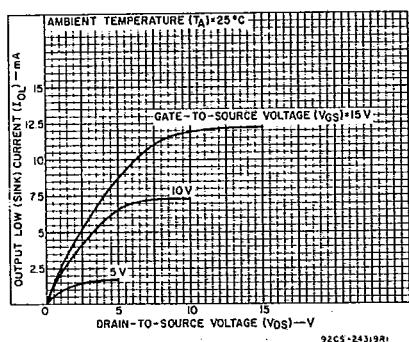
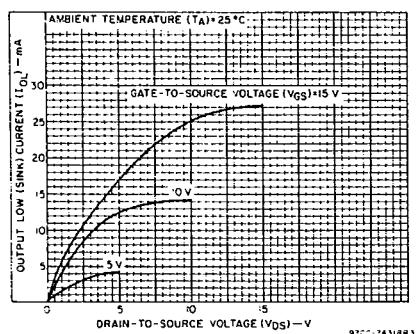
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DYNAMIC ELECTRICAL CHARACTERISTICS AT T<sub>A</sub> = 25°C, Input t<sub>r</sub>, t<sub>f</sub> = 20 ns, C<sub>L</sub> = 50 pF, R<sub>L</sub> = 200 kΩ

CHARACTERISTIC	TEST CONDITIONS		LIMITS			UNITS	
			V <sub>DD</sub> (V)	Min.	Typ.		
Propagation Delay Time (t <sub>PHL</sub> , t <sub>PLH</sub> )			5	—	180	360	ns
			10	—	75	150	
			15	—	60	120	
Transition Time (t <sub>THL</sub> , t <sub>TLH</sub> )			5	—	100	200	ns
			10	—	50	100	
			15	—	40	80	
Input Capacitance (C <sub>IN</sub> )	Any Input		—	5	7.5	pF	

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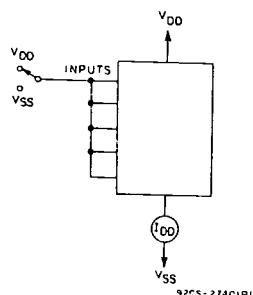


Fig. 7 — Quiescent device current test circuit.

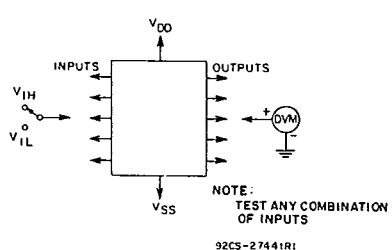


Fig. 8 — Input voltage test circuit.

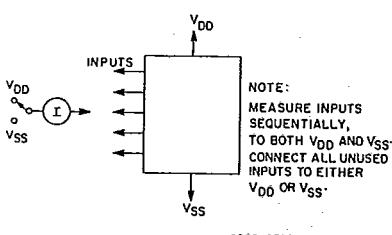
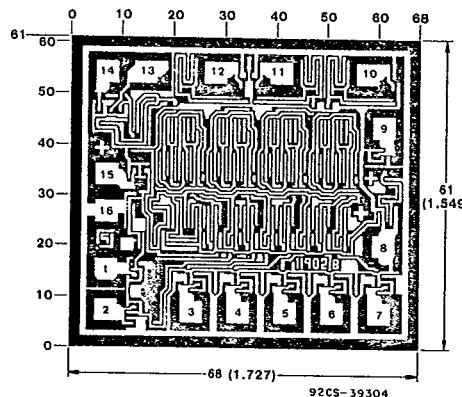


Fig. 9 — Input current test circuit.



Chip dimensions and pad layout for CD4519B.

*Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).*

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